

SEMICONDUCTOR TECHNICAL DATA

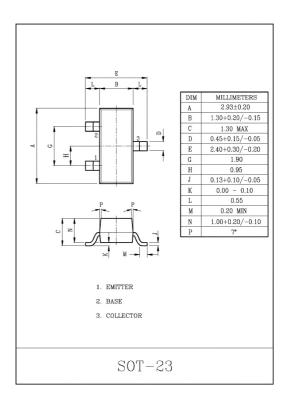
BCW31/32 EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION. SWITCHING APPLICATION.

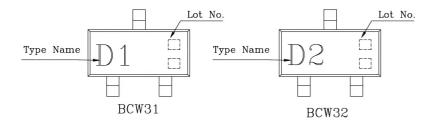
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	V _{CBO}	30	V	
Collector-Emitter Voltage	V_{CEO}	20	V	
Emitter-Base Voltage	V_{EBO}	5	V	
Collector Current	$I_{\mathbb{C}}$	100	mA	
Collector Power Dissipation	Pc *	350	mW	
Junction Temperature	$T_{\rm j}$	150	°C	
Storage Temperature Range	T_{stg}	-55~150	C	





Marking



BCW31/32

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage		V_{CBO}	I _C =10μA	30	-	-	V
Collector-Emitter Breakdown Voltage		V_{CEO}	I _C =2mA	20	-	-	V
Emitter-Base Breakdown Voltage		$ m V_{EBO}$	$I_{\rm E}$ =10 $\mu{ m A}$	5	-	_	V
Collector Cut-off Current		I_{CBO}	V_{CB} =30 V	-	-	100	nA
Emitter Cut-off Current		I_{EBO}	$ m V_{EB}$ =5 $ m V$	-	-	100	nA
DC Current Gain	BCW31	- h _{FE}	V_{CE} =5V, I_{C} =2mA	110	_	220	
	BCW32			200	_	450	
Collector-Emitter Saturation Voltage		$V_{\text{CE(sat)}}$	I_C =10mA, I_B =0.5mA	_	_	0.25	V
Base-Emitter On Voltage		V _{BE(ON)}	V_{CE} =5V, I_{C} =2mA	0.55	_	0.7	V
Collector Output Capacitance		C_{ob}	V_{CB} =10V, I_{E} =0, f =1MHz	-	-	4	рF
Noise Figure		NF	V_{CE} =5V, I_{C} =0.2mA R_{S} =2k Ω , f =1kHz	-	-	10	dB